

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

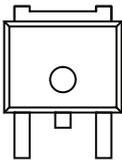


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY	
V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0155
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.0200
I_D (A)	- 50
Configuration	Single

FEATURES

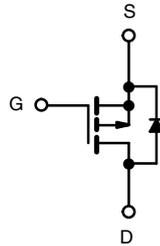
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

TO-252


G D S

Top View

Drain Connected to Tab



P-Channel MOSFET

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P06-15L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	$T_C = 25$ °C	- 50	A
	$T_C = 125$ °C	- 38	
Continuous Source Current (Diode Conduction) ^a	I_S	- 50	
Pulsed Drain Current ^b	I_{DM}	- 200	
Single Pulse Avalanche Current	I_{AS}	- 52	
Single Pulse Avalanche Energy	E_{AS}	135	
Maximum Power Dissipation ^b	$T_C = 25$ °C	136	W
	$T_C = 125$ °C	45	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$		-60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$		-1.5	-	-2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}$	$V_{DS} \geq -5\text{ V}$	-50	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -17\text{ A}$	-	0.0135	0.0155	Ω
		$V_{GS} = -10\text{ V}$	$I_D = -50\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	0.026	
		$V_{GS} = -10\text{ V}$	$I_D = -50\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	0.032	
		$V_{GS} = -4.5\text{ V}$	$I_D = -14\text{ A}$	-	0.017	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -17\text{ A}$		-	50	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	-	4730	5910	pF
Output Capacitance	C_{oss}			-	485	606	
Reverse Transfer Capacitance	C_{rss}			-	330	410	
Total Gate Charge ^c	Q_g	$V_{GS} = -10\text{ V}$	$V_{DS} = -30\text{ V}$, $I_D = -50\text{ A}$	-	98	150	nC
Gate-Source Charge ^c	Q_{gs}			-	15	23	
Gate-Drain Charge ^c	Q_{gd}			-	21	32	
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.47	2.9	4.42	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $R_L = 0.6\text{ }\Omega$ $I_D \cong -50\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 6.0\text{ }\Omega$		-	15	18	ns
Rise Time ^c	t_r			-	12	16	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	112	125	
Fall Time ^c	t_f			-	39	48	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	-200	A
Forward Voltage	V_{SD}	$I_F = -50\text{ A}$, $V_{GS} = 0\text{ V}$		-	-0.8	-1.5	V

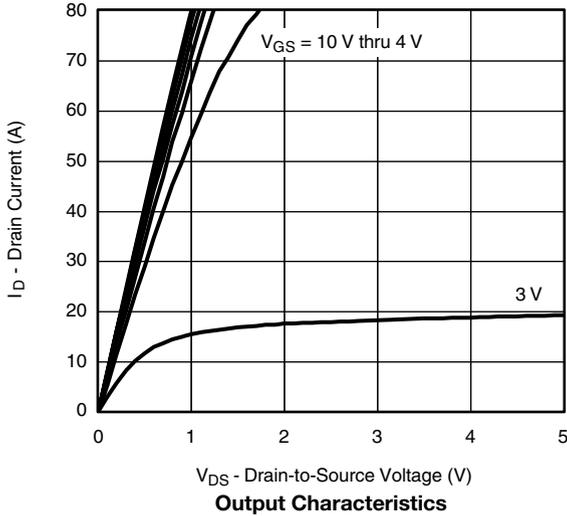
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

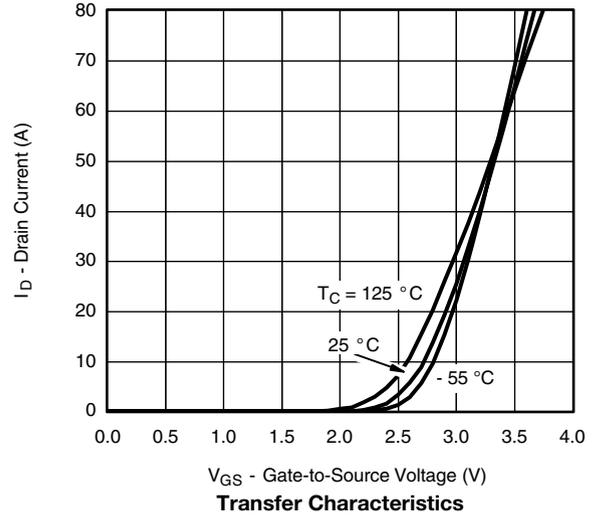
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



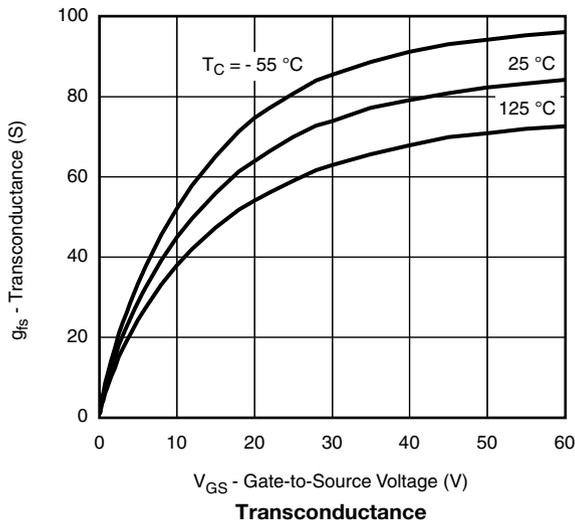
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



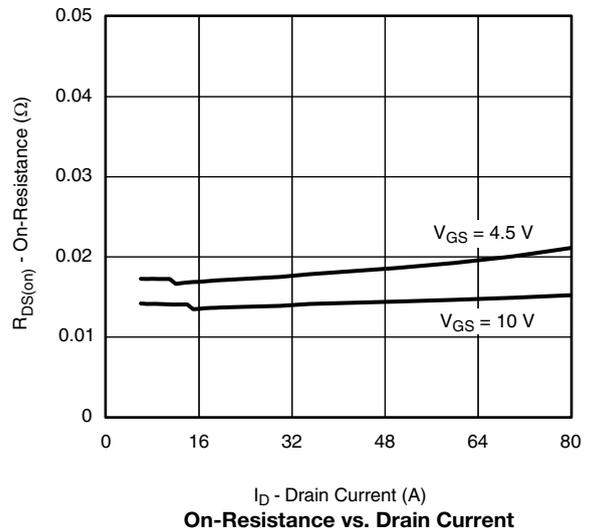
Output Characteristics



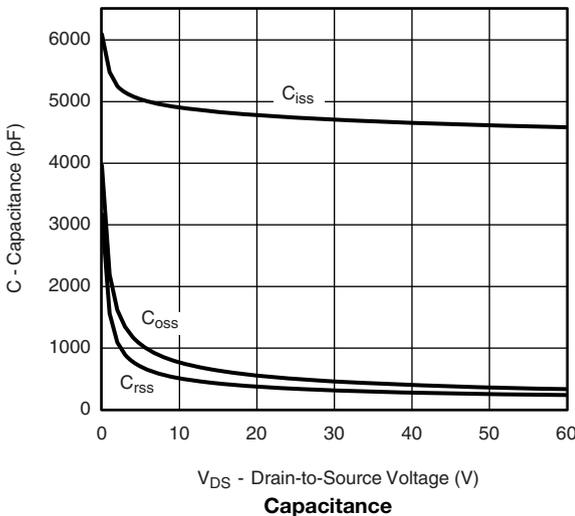
Transfer Characteristics



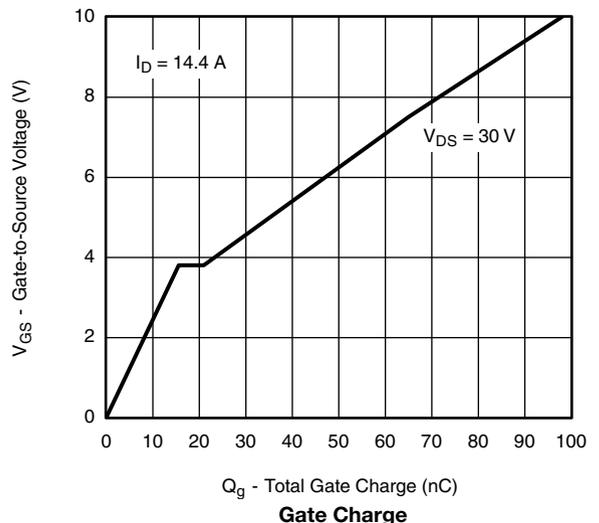
Transconductance



On-Resistance vs. Drain Current



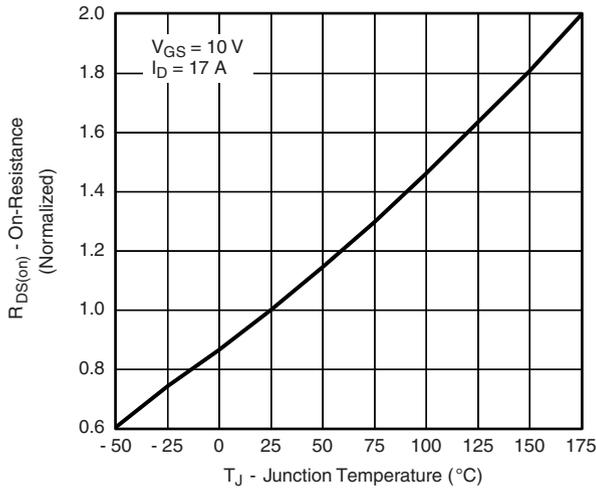
Capacitance



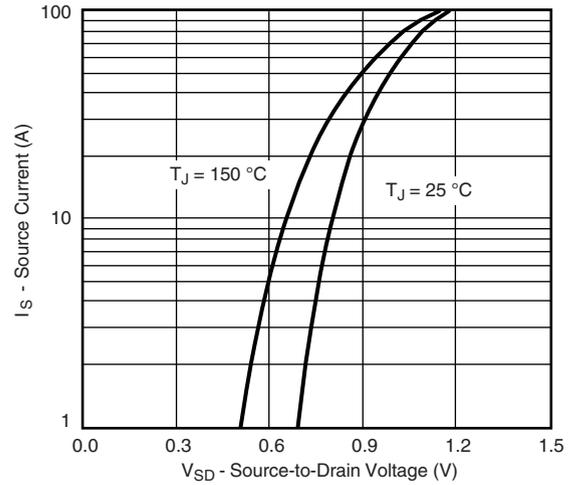
Gate Charge



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

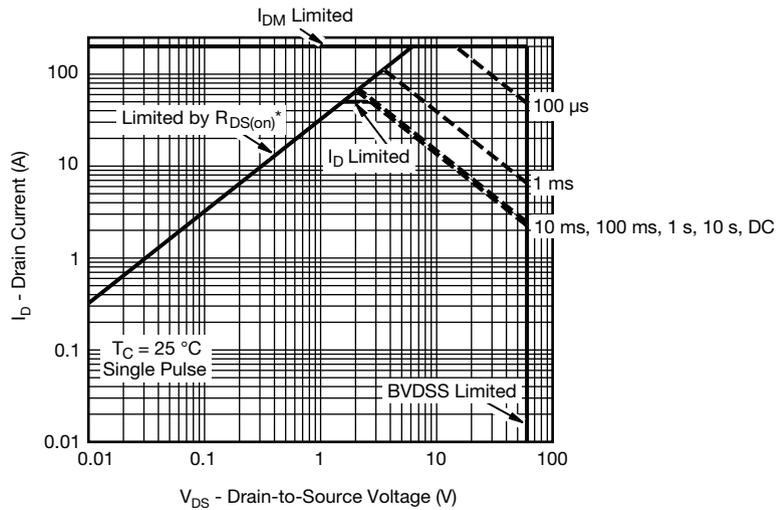


On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

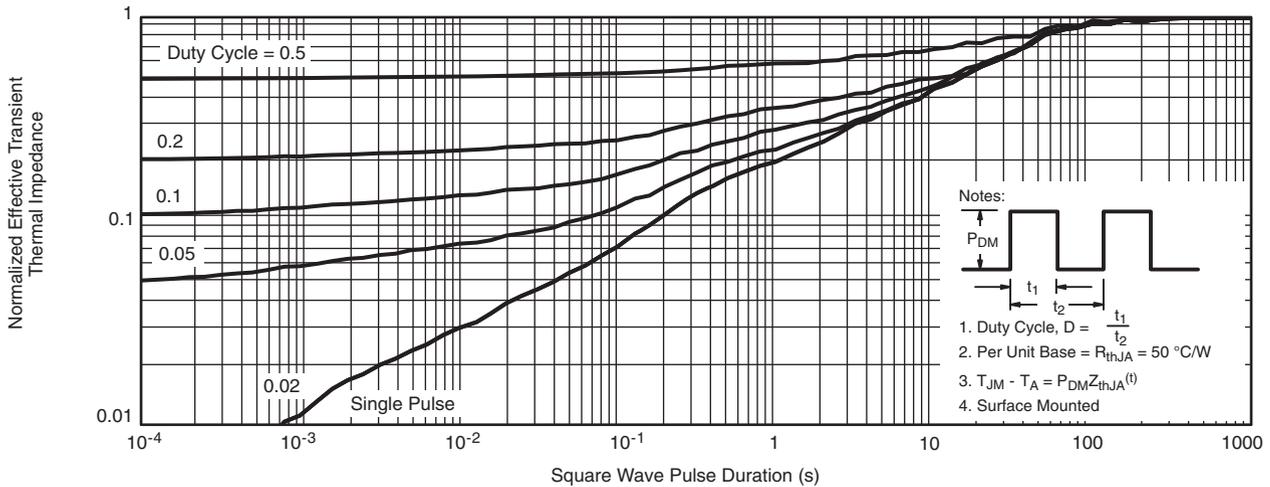


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

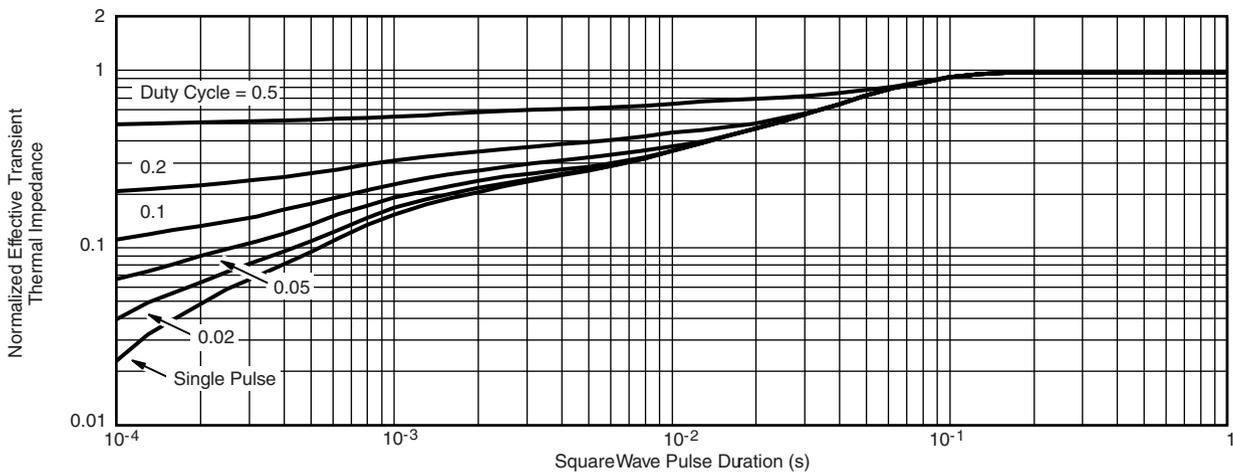
Safe Operating Area



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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DPAK / TO-252 and Reverse DPAK

Ordering codes for the SQ rugged series power MOSFETs in the DPAK / TO-252 and Reverse DPAK packages:

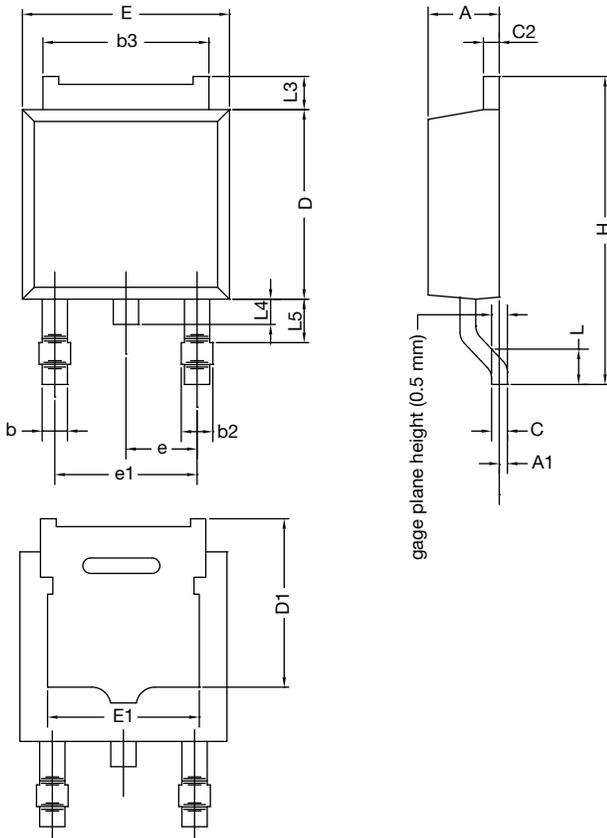
Table with 3 columns: DATASHEET PART NUMBER, OLD ORDERING CODE a, NEW ORDERING CODE. Lists various MOSFET part numbers and their corresponding ordering codes.

Note

a. Old ordering code is obsolete and no longer valid for new orders



TO-252AA Case Outline

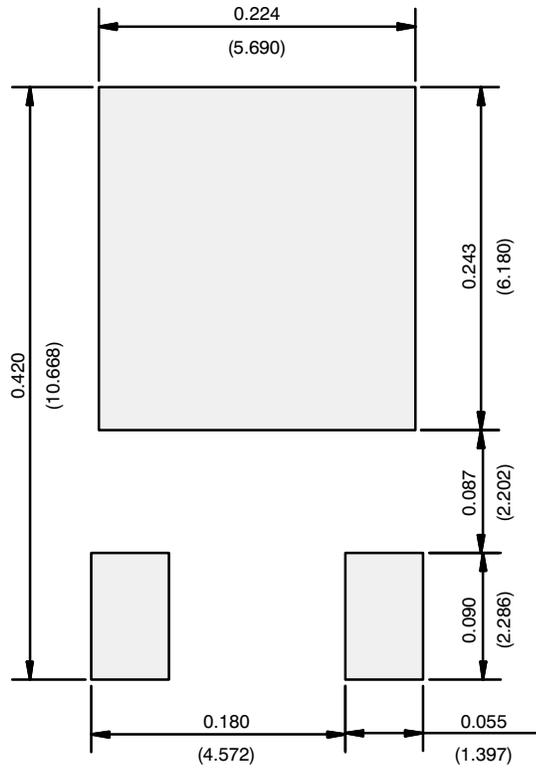


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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